

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 03-219000

(43)Date of publication of application : 26.09.1991

(51)Int.Cl.

C30B 33/10
H01L 21/304
H01L 21/308

(21)Application number : 02-214290

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(22)Date of filing : 15.08.1990

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(30)Priority

Priority number : 01289937 Priority date : 09.11.1989 Priority country : JP

(54) ETCHING METHOD AND WASHING METHOD FOR SILICON WAFER

(57)Abstract:

PURPOSE: To extremely decrease metallic contaminating materials contg. Fe by etching a silicon wafer with an etching soln. prepd. by adding a complexing agent which forms a complex compd. with the metallic contaminating materials to an aq. alkaline soln.

CONSTITUTION: The silicon wafer is etched or washed by using the etching liquid or washing liquid or the etching liquid or washing liquid added with the complexing agent (e.g.: citric acid) which forms the complex compd. with an extremely slight quantity of the metallic contaminating material, for example, Fe, existing on the surface of the silicon wafer at the time of etching or washing the silicon wafer by using the aq. alkaline soln., for example, an aq. KOH soln. and ammonia-aq. hydrogen peroxide soln. The degradation in the quality of the silicon wafer is averted in this way and the deterioration in the electrical characteristics when the silicon wafer is used for highly integrated devices is averted.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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